

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max $T_A = +25^\circ\text{C}$
60V	18m Ω @ $V_{GS} = 10\text{V}$	9.2 A
	28m Ω @ $V_{GS} = 4.5\text{V}$	7.5 A

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and maintain superior switching performance, making it ideal for high efficiency power management applications.

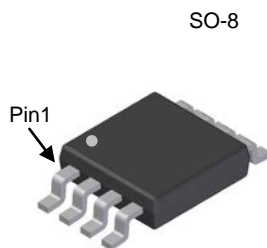
- Load Switch
- Adaptor Switch
- Notebook PC

Features and Benefits

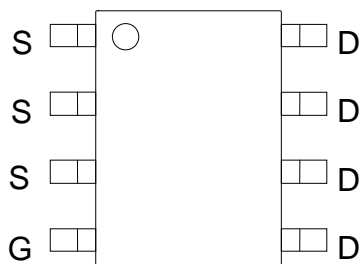
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

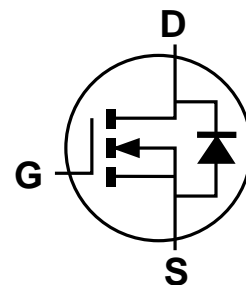
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish — Matte Tin annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.076 grams (approximate)



Top View



Pin-Out
Top View



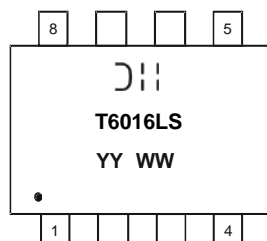
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT6016LSS-13	SO-8	2500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



DII = Manufacturer's Marking
T6016LS = Product Type Marking Code
YYWW = Date Code Marking
YY or **YY** = Year (ex: 14 = 2014)
WW = Week (01 - 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	60	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	9.2 7.4	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	11.9 9.5	A
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	7.5 6.0	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	9.7 7.7	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I _{DM}	60	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	2	A
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	15.3	A
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	11.7	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Total Power Dissipation (Note 5)			P _D	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		R _{θJA}	85	°C/W
	t < 10s		R _{θJA}	45	°C/W
Total Power Dissipation (Note 6)			P _D	2.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		R _{θJA}	74	°C/W
	t < 10s		R _{θJA}	37	°C/W
Thermal Resistance, Junction to Case			R _{θJC}	13	°C/W
Operating and Storage Temperature Range			T _J , T _{STG}	-55 to 150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 48V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	1	—	2.5	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(on)}	—	—	18	mΩ	V _{GS} = 10V, I _D = 10A V _{GS} = 4.5V, I _D = 6A
		—	—	28		
Diode Forward Voltage (Note 7)	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iSS}	—	864	—	pF	V _{DS} = 30V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{oss}	—	282	—		
Reverse Transfer Capacitance	C _{rSS}	—	27	—		
Gate resistance	R _g	—	1.3	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	8.4	—	nC	V _{DS} = 30V, I _D = 10A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	17	—		
Gate-Source Charge	Q _{gs}	—	3.1	—		
Gate-Drain Charge	Q _{gd}	—	4.3	—		
Turn-On Delay Time	t _{D(on)}	—	3.4	—	ns	V _{GS} = 10V, V _{DS} = 30V, R _G = 6Ω, I _D = 10A
Turn-On Rise Time	t _r	—	5.2	—		
Turn-Off Delay Time	t _{D(off)}	—	13	—		
Turn-Off Fall Time	t _f	—	7	—		
Reverse Recovery Time	T _{rr}	—	22	—	ns	I _F = 10A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{rr}	—	11	—	nC	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1 inch square copper plate.
 - I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

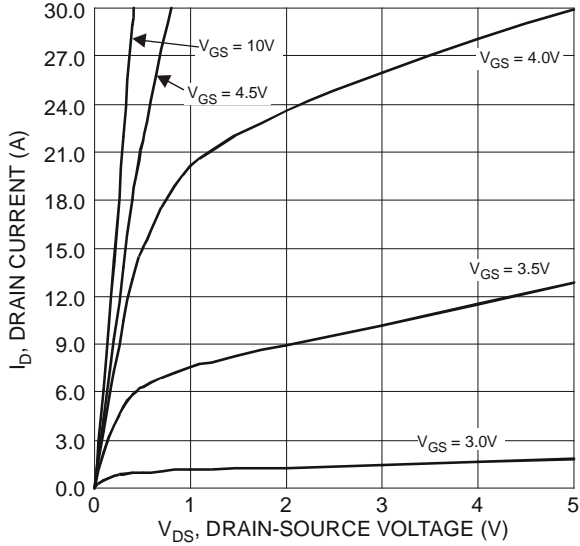


Figure 1 Typical Output Characteristics

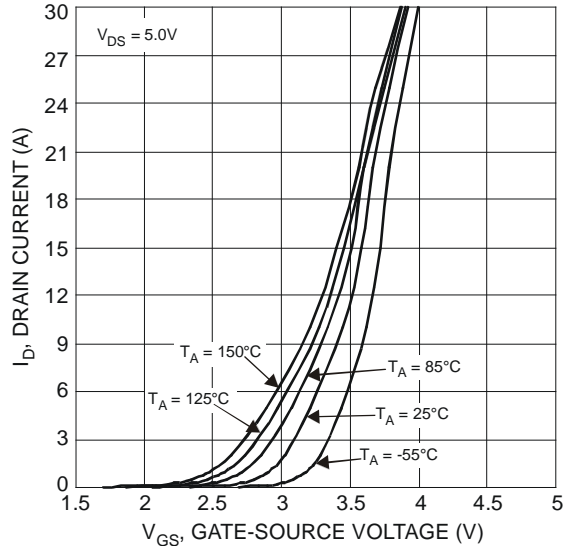


Figure 2 Typical Transfer Characteristics

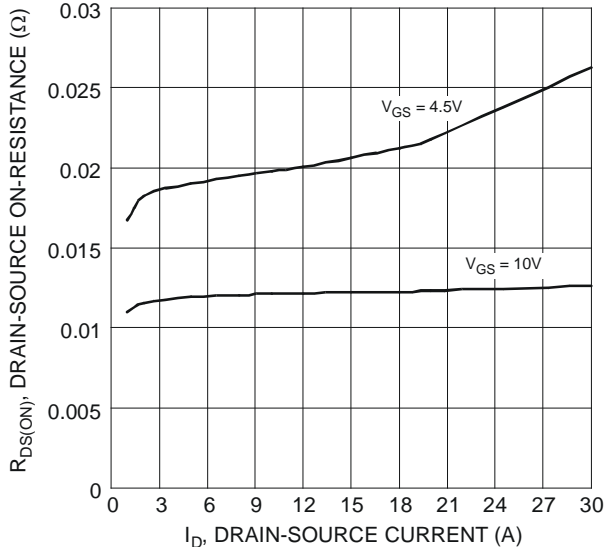


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

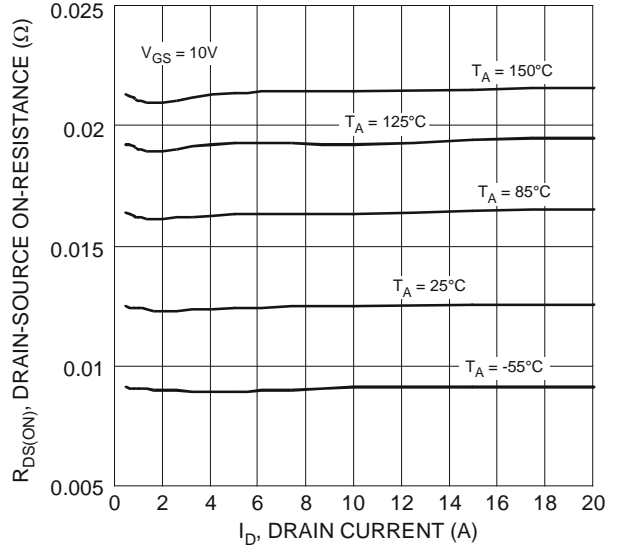


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

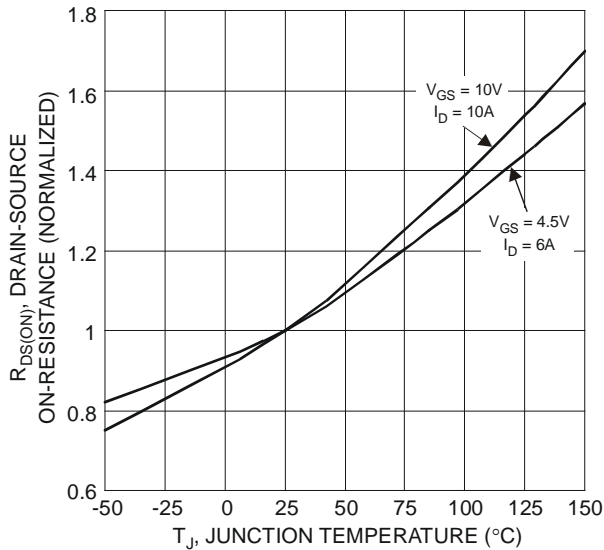


Figure 5 On-Resistance Variation with Temperature

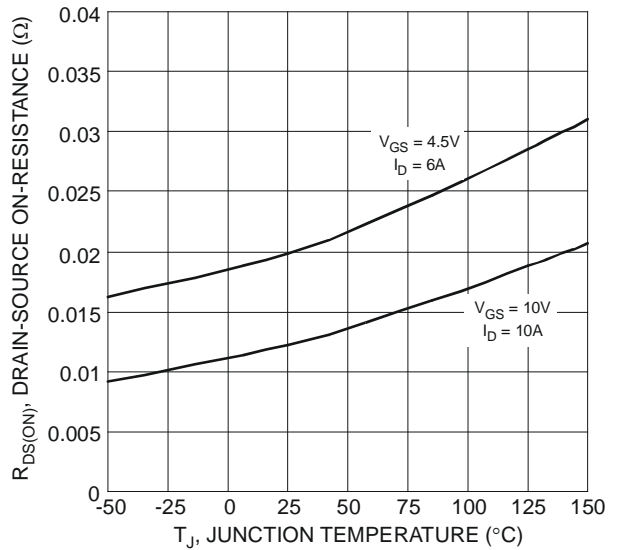


Figure 6 On-Resistance Variation with Temperature

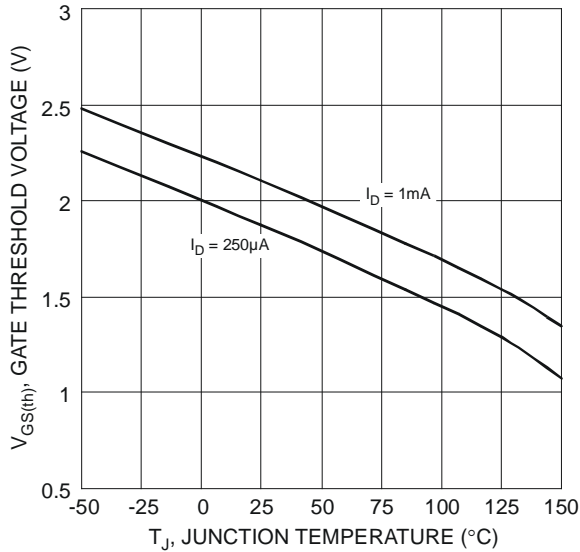


Figure 7 Gate Threshold Variation vs. Ambient Temperature

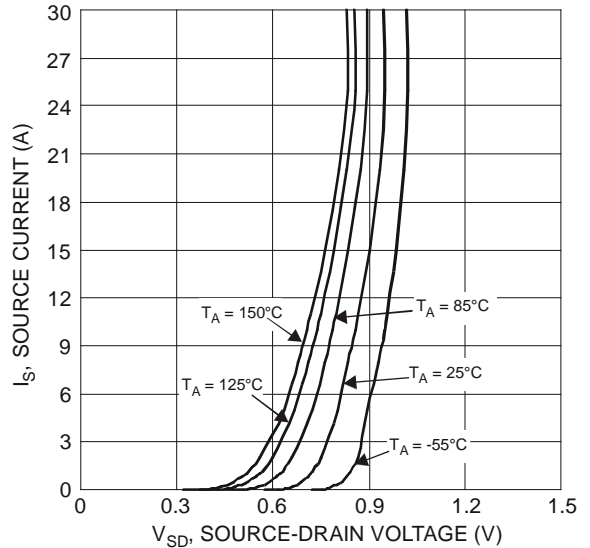


Figure 8 Diode Forward Voltage vs. Current

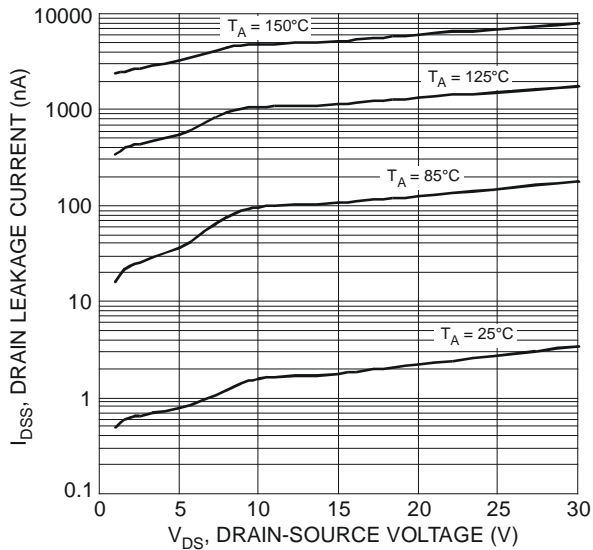


Figure 9 Typical Drain-Source Leakage Current vs. Voltage

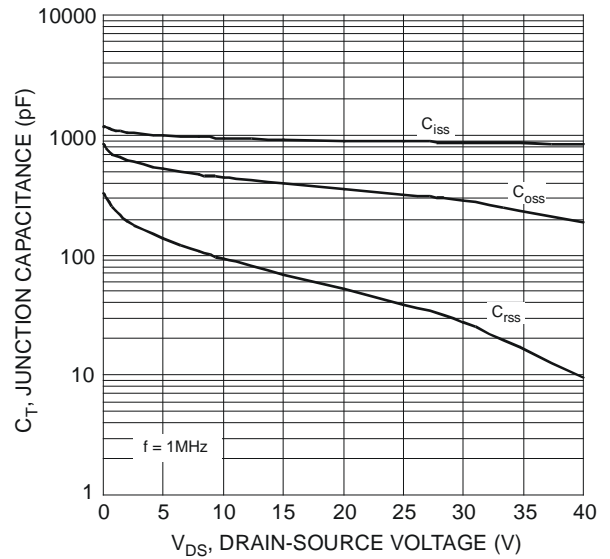


Figure 10 Typical Junction Capacitance

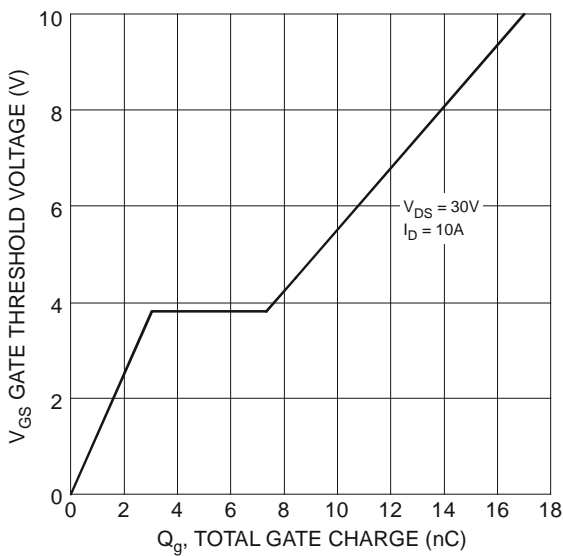


Figure 11 Gate Charge

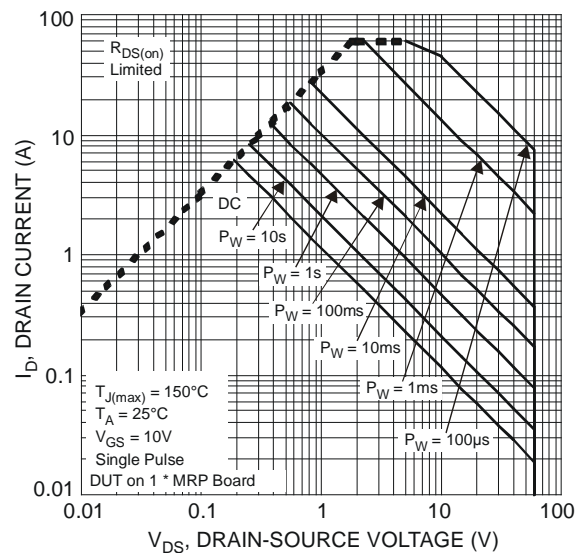


Figure 12 SOA, Safe Operation Area

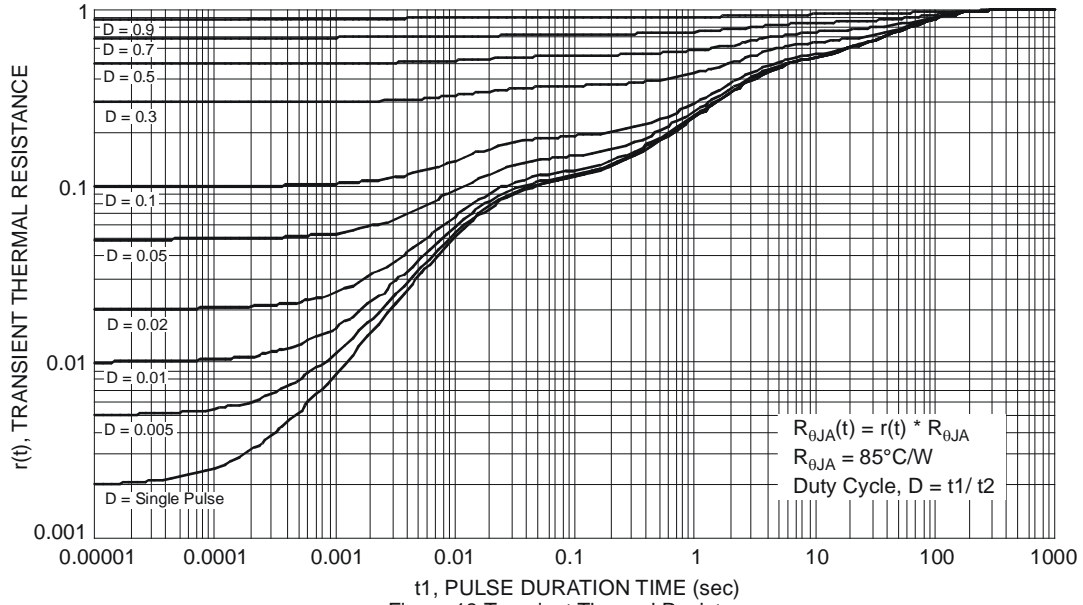
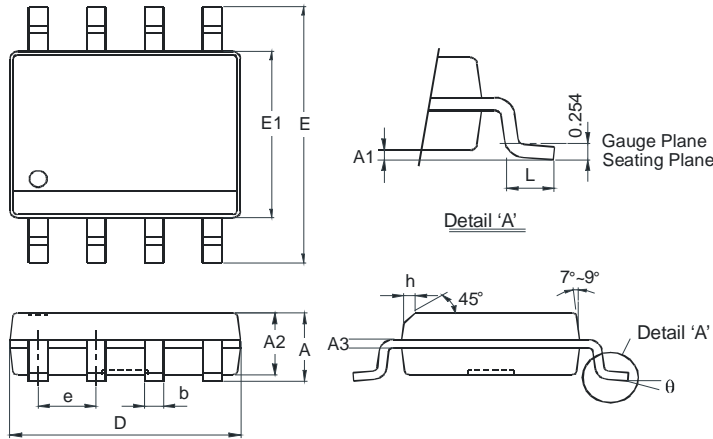


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

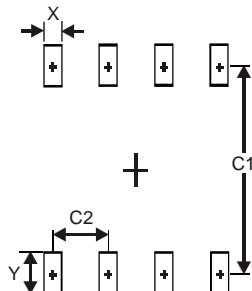
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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